



PG100 - PG1010

AXIAL LEADED SILICON RECTIFIER DIODES

VOLTAGE RANGE: 50 - 1000V

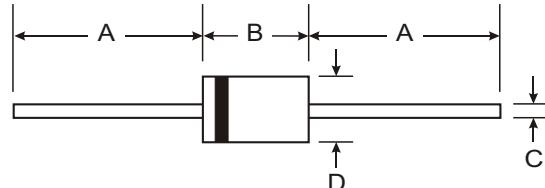
CURRENT: 1.0 A

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability

Mechanical Data

- Case: DO - 4 1
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



DO-41		
Dim	Min	Max
A	25.40	—
B	4.06	5.21
C	0.71	0.864
D	2.00	2.72

All Dimensions in mm

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	PG100	PG101	PG102	PG104	PG106	PG108	PG1010	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R								V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) $\text{@ } T_A = 75^\circ\text{C}$	I _O								A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}								A
Forward Voltage $\text{@ } I_F = 1.0\text{A}$	V _{FM}								V
Peak Reverse Current $\text{@ } T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage $\text{@ } T_A = 100^\circ\text{C}$	I _{RM}								μA
Typical Junction Capacitance (Note 2)	C _j								pF
Typical Thermal Resistance Junction to Ambient (Note 1)	R _{θ JA}								K/W
Operating Temperature Range	T _j								$^\circ\text{C}$
Storage Temperature Range	T _{STG}								$^\circ\text{C}$

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case

2. Measured at 1.0 MHz and Applied Reverse Voltage of 4.0V D.C.

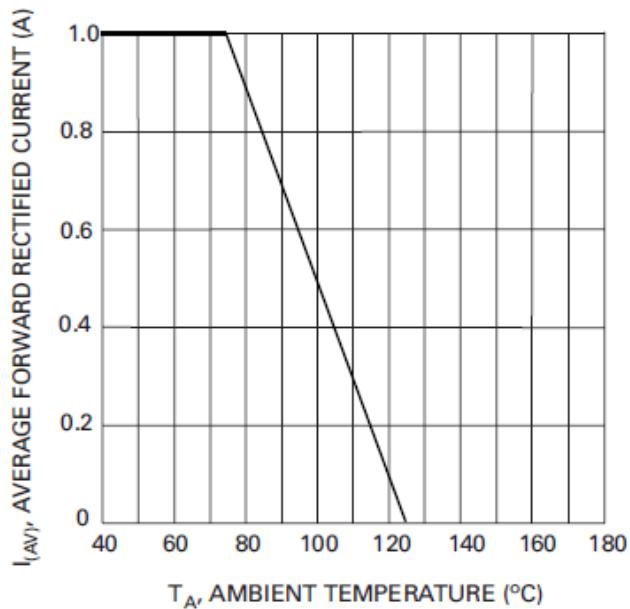
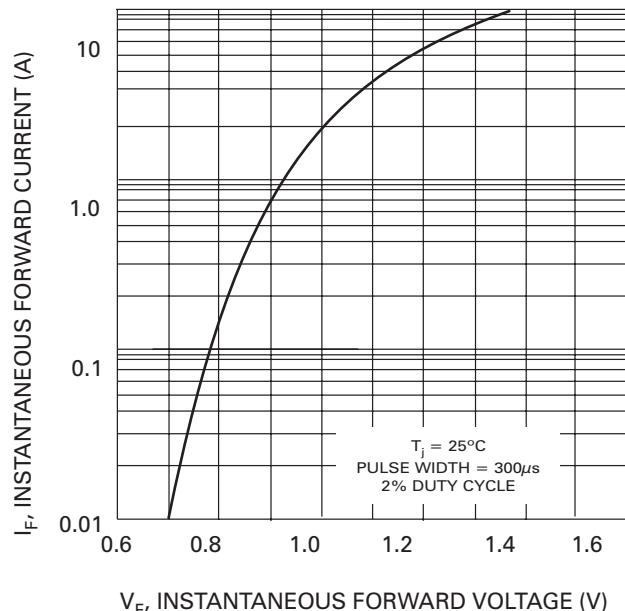


Fig. 1 Forward Current Derating Curve



V_F, INSTANTANEOUS FORWARD VOLTAGE (V)

Fig. 2 Typical Forward Characteristics

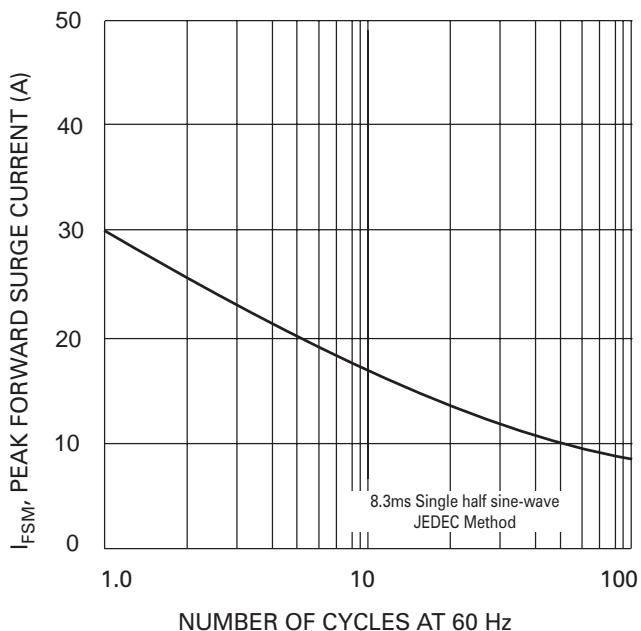


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

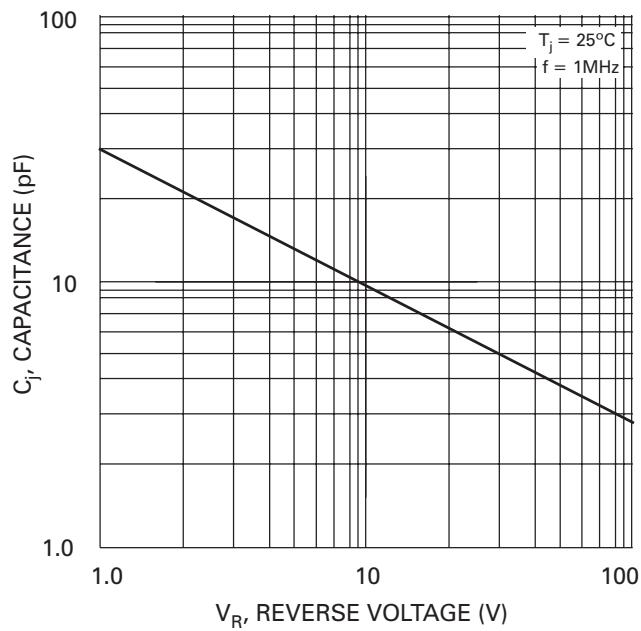


Fig. 4 Typical Junction Capacitance